MOSFETs Silicon N-channel MOS (U-MOSVII)

TPN6R303NC

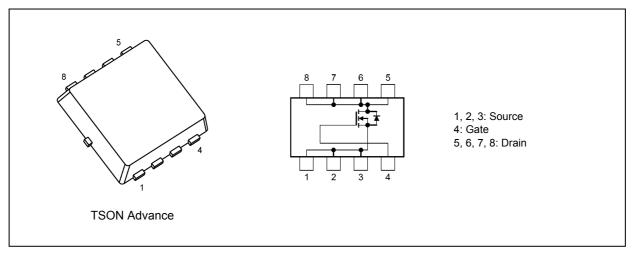
1. Applications

- Lithium-Ion Secondary Batteries
- Power Management Switches

2. Features

- (1) Small, thin package
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 5.2 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (3) Low leakage current: I_{DSS} = 10 μ A (max) (V_{DS} = 30 V)
- (4) Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_{D} = 0.2 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteris	stics		Symbol	Rating	Unit
Drain-source voltage			V _{DSS}	30	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)	(Silicon limit)	(Note 1)	I _D	43	A
Drain current (DC)		(Note 1)	Ι _D	20	
Drain current (pulsed)	(1 ms)	(Note 1)	I _{DP}	107	
Power dissipation	(T _c = 25°C)		PD	19	W
Power dissipation	(t = 10 s)	(Note 2)	PD	1.9	
Power dissipation	(t = 10 s)	(Note 3)	PD	0.7	
Single-pulse avalanche energy		(Note 4)	E _{AS}	51	mJ
Avalanche current			I _{AR}	20	A
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

5. Thermal Characteristics

Character	istics		Symbol	Max	Unit
Channel-to-case thermal resistance	(T _c = 25°C)		R _{th(ch-c)}	6.57	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 2)	R _{th(ch-a)}	65.7	
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R _{th(ch-a)}	178	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 0.099 mH, I_{AR} = 20 A

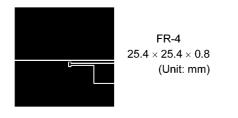


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

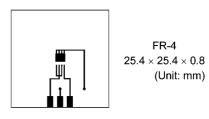


Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

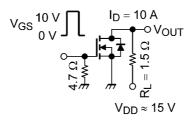
6.1. Static Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_	_	±0.1	μA
Drain cut-off current	I _{DSS}	V_{DS} = 30 V, V_{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	30	_	—	V
Drain-source breakdown voltage (Note 5)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	15	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.2 mA	1.3	_	2.3	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 10 A	_	6.9	8.4	mΩ
		V _{GS} = 10 V, I _D = 10 A		5.2	6.3	

Note 5: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		1370	_	pF
Reverse transfer capacitance	C _{rss}]	_	110	—	
Output capacitance	C _{oss}			420	—	
Switching time (rise time)	tr	See Figure 6.2.1.		6.0	_	ns
Switching time (turn-on time)	t _{on}]	_	14	—	
Switching time (fall time)	t _f]		14	_	
Switching time (turn-off time)	t _{off}			55	_	



 $Duty \leq 1\%, \ t_w = 10 \ \mu s$ Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

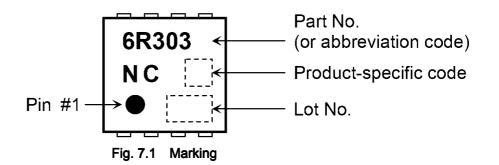
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 24$ V, V_{GS} = 10 V, I_D = 20 A		24	—	nC
Gate-source charge 1	Q _{gs1}		_	5	_	
Gate-drain charge	Q _{gd}			5.4	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

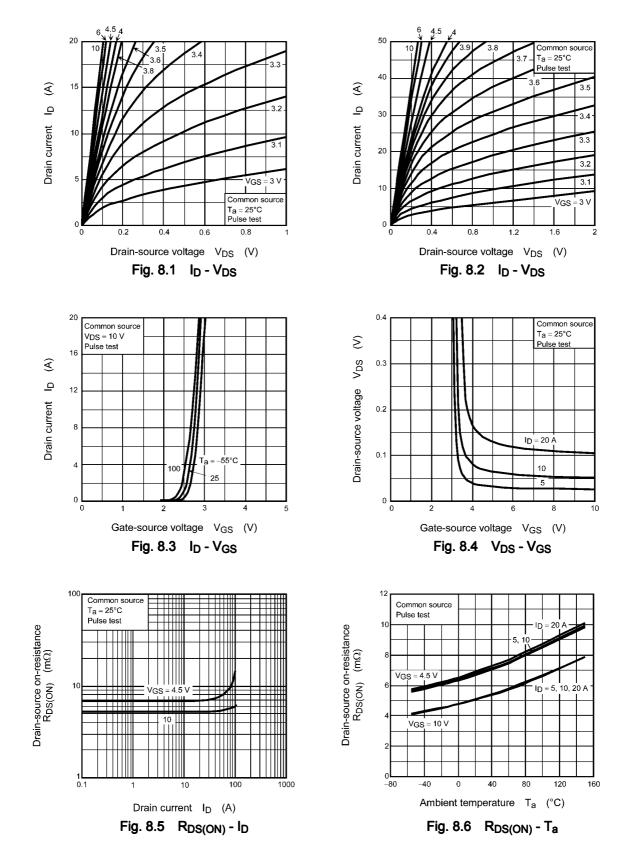
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 6)	I _{DRP}	—	_	—	107	А
Diode forward voltage	V _{DSF}	I _{DR} = 20 A, V _{GS} = 0 V		_	-1.2	V

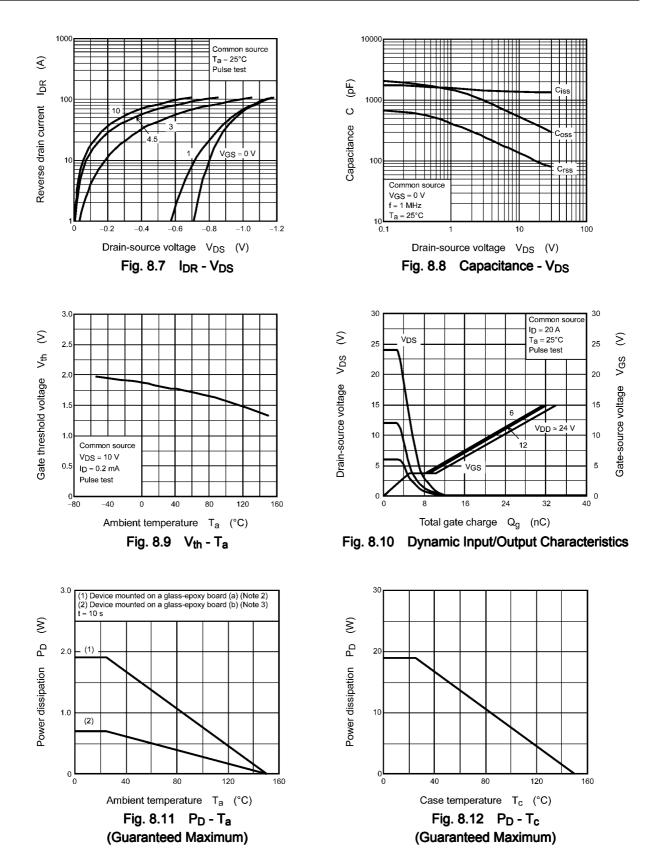
Note 6: Ensure that the channel temperature does not exceed 150°C.

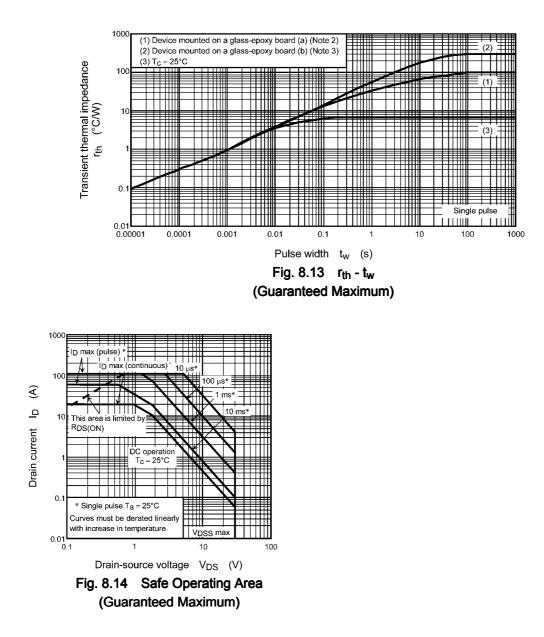
7. Marking



8. Characteristics Curves (Note)







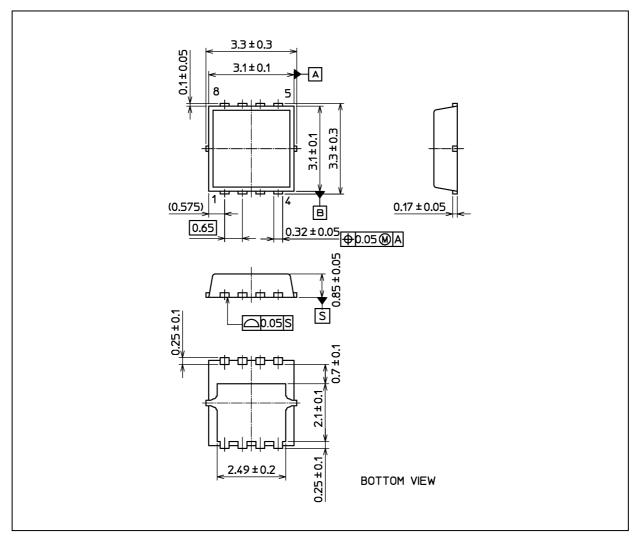
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TPN6R303NC

Package Dimensions

Unit: mm



Weight: 0.02 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance

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